

IMFEDK 2014 Awards

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Authors: **Chaiyanan Kulchaisit, Mami Fujii, Yoshihiro Ueoka,
Juan PaoloBermundo, Masahiro Horita, Yasuaki Ishikawa,
and YukiharuUraoka** Paper ID: B-3
Title: “Reliability of Bottom Gate Amorphous InGaZnO Thin-Film Transistors
with Siloxane Passivation Layer”
Affiliation: Nara Institute of Science and Technology

■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Hiroshi Oka** Paper ID: PA-01
Title: “Schottky Barrier Height Reduction of NiGe/Ge Junction by P Ion
Implantation for Metal Source/Drain Ge CMOS Devices”
Coauthors: Yuya Minoura, Takuji Hosoi, Takayoshi Shimura and Heiji Watanabe
Affiliation: Osaka University

Author: **Takuma Kobayashi** Paper ID: PB-01
Title: “Conduction-Type Dependence of Thermal Oxidation Rate on SiC(0001)”
Coauthors: Jun Suda and Tsunenobu Kimoto
Affiliation: Kyoto University

Author: **Takuya Kakegami** Paper ID: PB-02
Title: “Study of current collapse in AlGaIn/GaN HEMTs passivated with
sputter-deposited SiO₂ and SiN_x”
Coauthors: Shintaro Ohi, Hirokuni Tokuda and Masaaki Kuzuhara
Affiliation: University of Fukui

Author: **Go Wakimura** Paper ID: PB-03
Title: “Mechanism of off-leakage current in InGaZnO thin-film transistors”
Coauthors: Yoshimitsu Yamauchi, Toshimasa Matsuoka and Yoshinari Kamakura
Affiliation: Osaka University

Author: **Takahiro Yamaguchi** Paper ID: PC-03
Title: “Noise Performance of an Implantable Self-reset CMOS Image Sensor”
Coauthors: Yoshinori Sunaga, Makito Haruta, Toshihiko Noda, Kiyotaka Sasagawa,
Takashi Tokuda and Jun Ohta
Affiliation: Nara Institute of Science and Technology

■ IEEE SSCS Kansai Chapter IMFEDK Student Paper Award

Author: **Hitoshi Kunitake** Paper ID: PD-01
Title: “Design of Millimeter-Wave CMOS Transmission-Line-to-Waveguide
Transitions”
Coauthors: Kyoya Takano, Mizuki Motoyoshi, Kosuke Katayama, Shuhei Amakawa,
Takeshi Yoshida and Minoru Fujishima
Affiliation: Hiroshima University

